

# 1.5V Drive Pch MOSFET

## RZR040P01

### ●Structure

Silicon P-channel MOSFET

### ●Features

- 1) Low on-resistance.
- 2) High power package.
- 3) Low voltage drive. (1.5V)

### ●Applications

Switching

### ●Packaging specifications

| Type      | Package                      | Taping |
|-----------|------------------------------|--------|
|           | Code                         | TL     |
|           | Basic ordering unit (pieces) | 3000   |
| RZR040P01 |                              | ○      |

### ●Absolute maximum ratings (Ta=25°C)

| Parameter                      |            | Symbol      | Limits      | Unit |
|--------------------------------|------------|-------------|-------------|------|
| Drain-source voltage           |            | $V_{DS}$    | -12         | V    |
| Gate-source voltage            |            | $V_{GS}$    | ±10         | V    |
| Drain current                  | Continuous | $I_D$       | ±4          | A    |
|                                | Pulsed     | $I_{DP}$ *1 | ±16         | A    |
| Source current<br>(Body diode) | Continuous | $I_S$       | -0.8        | A    |
|                                | Pulsed     | $I_{SP}$ *1 | -16         | A    |
| Total power dissipation        |            | $P_D$ *2    | 1.0         | W    |
| Channel temperature            |            | $T_{ch}$    | 150         | °C   |
| Range of Storage temperature   |            | $T_{stg}$   | -55 to +150 | °C   |

 \*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$ 

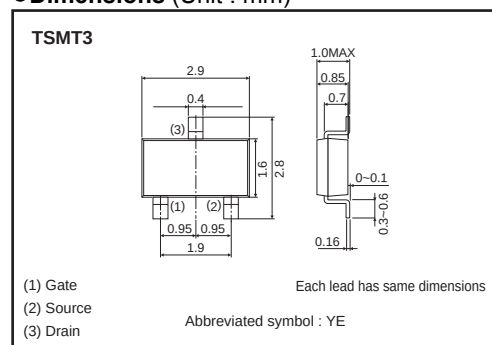
\*2 When mounted on a ceramic board

### ●Thermal resistance

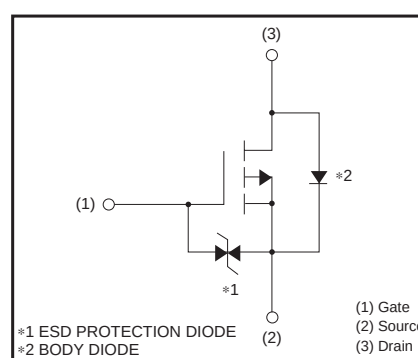
| Parameter          | Symbol           | Limits | Unit   |
|--------------------|------------------|--------|--------|
| Channel to ambient | $R_{th(ch-a)}$ * | 125    | °C / W |

\* When mounted on a ceramic board.

### ●Dimensions (Unit : mm)



### ●Inner circuit



## ●Electrical characteristics (Ta=25°C)

| Parameter                               | Symbol         | Min. | Typ. | Max.     | Unit       | Conditions                                 |
|-----------------------------------------|----------------|------|------|----------|------------|--------------------------------------------|
| Gate-source leakage                     | $I_{GSS}$      | –    | –    | $\pm 10$ | $\mu A$    | $V_{GS}=\pm 10V$ , $V_{DS}=0V$             |
| Drain-source breakdown voltage          | $V_{(BR) DSS}$ | –12  | –    | –        | V          | $I_D = -1mA$ , $V_{GS}=0V$                 |
| Zero gate voltage drain current         | $I_{DSS}$      | –    | –    | –1       | $\mu A$    | $V_{DS} = -12V$ , $V_{GS}=0V$              |
| Gate threshold voltage                  | $V_{GS(th)}$   | –0.3 | –    | –1.0     | V          | $V_{DS} = -6V$ , $I_D = -1mA$              |
| Static drain-source on-state resistance | $R_{DS(on)}$ * | –    | 22   | 30       | m $\Omega$ | $I_D = -4A$ , $V_{GS} = -4.5V$             |
|                                         |                | –    | 30   | 42       | m $\Omega$ | $I_D = -2A$ , $V_{GS} = -2.5V$             |
|                                         |                | –    | 40   | 60       | m $\Omega$ | $I_D = -2A$ , $V_{GS} = -1.8V$             |
|                                         |                | –    | 55   | 110      | m $\Omega$ | $I_D = -0.8A$ , $V_{GS} = -1.5V$           |
| Forward transfer admittance             | $ Y_{fs} $ *   | 6.5  | –    | –        | S          | $V_{DS} = -6V$ , $I_D = -4A$               |
| Input capacitance                       | $C_{iss}$      | –    | 2350 | –        | pF         | $V_{DS} = -6V$                             |
| Output capacitance                      | $C_{oss}$      | –    | 310  | –        | pF         | $V_{GS}=0V$                                |
| Reverse transfer capacitance            | $C_{rss}$      | –    | 280  | –        | pF         | $f=1MHz$                                   |
| Turn-on delay time                      | $t_{d(on)}$ *  | –    | 11   | –        | ns         | $V_{DD} \doteq -6V$                        |
| Rise time                               | $t_r$ *        | –    | 70   | –        | ns         | $I_D = -2A$                                |
| Turn-off delay time                     | $t_{d(off)}$ * | –    | 380  | –        | ns         | $V_{GS} = -4.5V$                           |
| Fall time                               | $t_f$ *        | –    | 210  | –        | ns         | $R_L \doteq 3\Omega$                       |
| Total gate charge                       | $Q_g$ *        | –    | 30   | –        | nC         | $V_{DD} \doteq -6V$ $R_L \doteq 1.5\Omega$ |
| Gate-source charge                      | $Q_{gs}$ *     | –    | 4.0  | –        | nC         | $I_D = -4A$ $R_G=10\Omega$                 |
| Gate-drain charge                       | $Q_{gd}$ *     | –    | 3.5  | –        | nC         | $V_{GS} = -4.5V$                           |

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

| Parameter       | Symbol     | Min. | Typ. | Max. | Unit | Conditions                |
|-----------------|------------|------|------|------|------|---------------------------|
| Forward voltage | $V_{SD}$ * | –    | –    | –1.2 | V    | $I_S = -4A$ , $V_{GS}=0V$ |

\*Pulsed

# ●Electrical characteristics curves

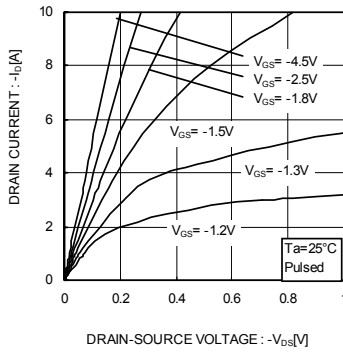


Fig.1 Typical output characteristics( I )

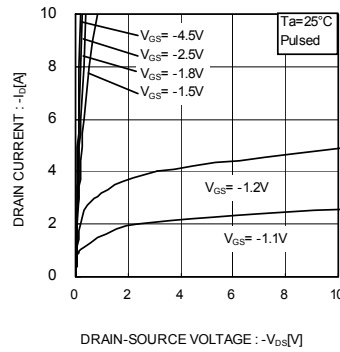


Fig.2 Typical output characteristics( II )

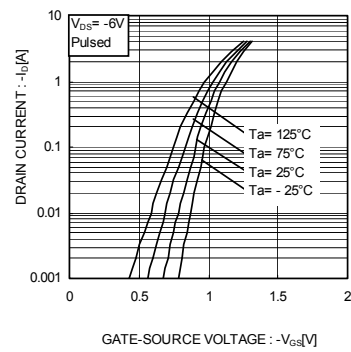


Fig.3 Typical Transfer Characteristics

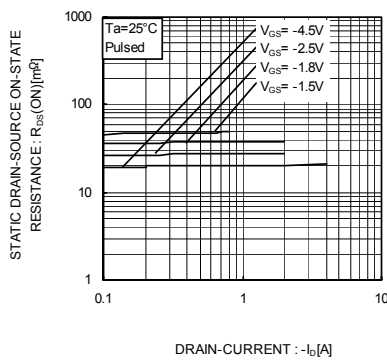


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

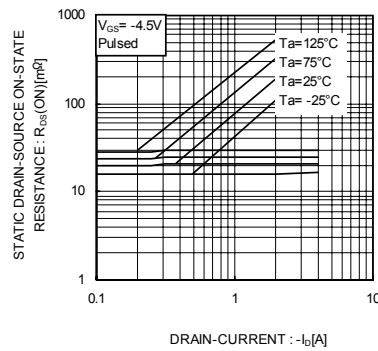


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )

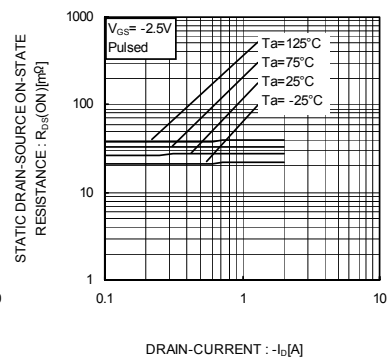


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

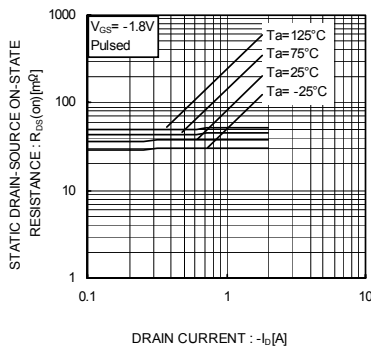


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

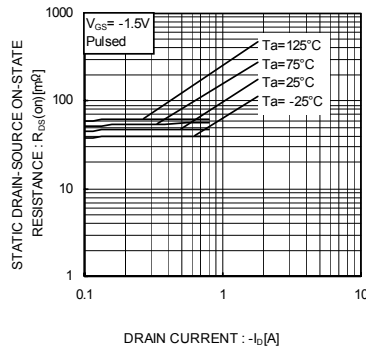


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current( V )

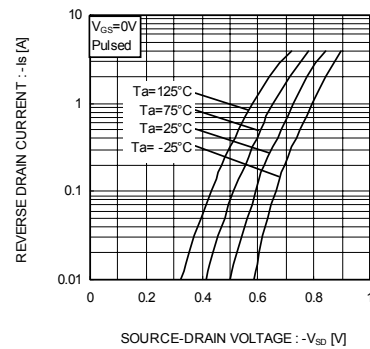


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

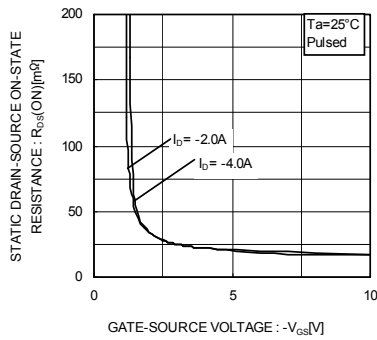


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

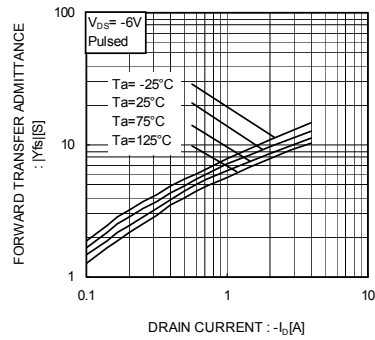


Fig.11 Forward Transfer Admittance vs. Drain Current

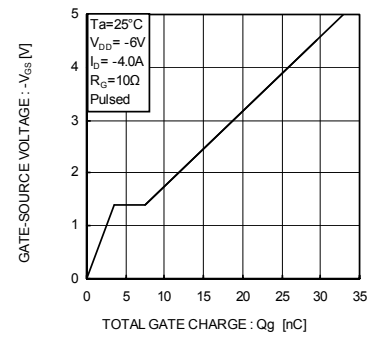


Fig.12 Dynamic Input Characteristics

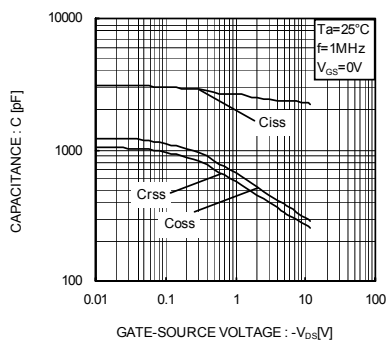


Fig.13 Typical Capacitance vs. Drain-Source Voltage

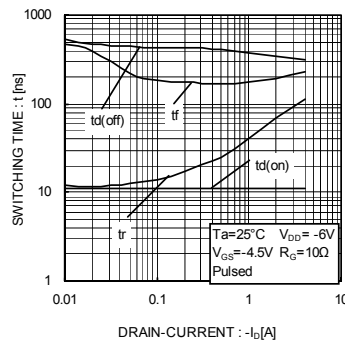


Fig.14 Switching Characteristics

## ●Measurement circuits

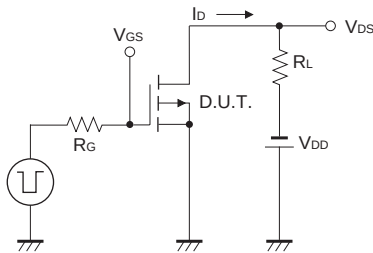


Fig.1-1 Switching Time Measurement Circuit

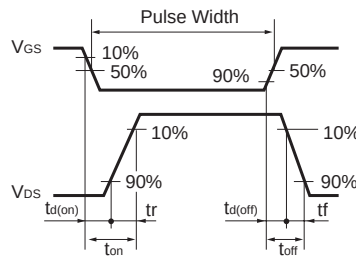


Fig.1-2 Switching Waveforms

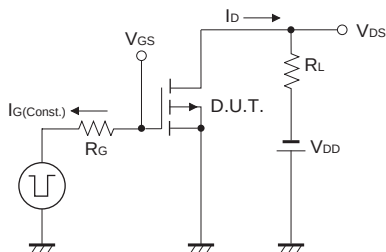


Fig.2-1 Gate Charge Measurement Circuit

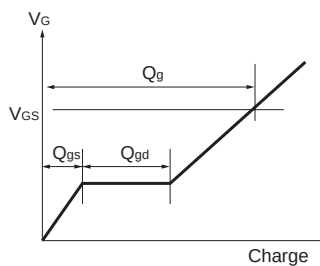


Fig.2-2 Gate Charge Waveform

## ●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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